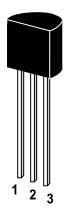
NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25℃)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	V
Base Current	I _B	30	mA
Collector Current	Ic	150	mA
Power Dissipation	P _{tot}	400	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	Ts	-55 to +125	°C







SEMTECH ELECTRONICS LTD.

ST 2SC732

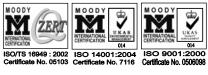
Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =6V, I _C =2mA			000		400	
	Current Gain Group G	h _{FE}	200 350	-	400 700	-
Base-Emitter Voltage	L	h _{FE}	350	-	700	-
at V _{CE} =6V,I _C =2mA		V_{BE}	-	0.65	-	V
Collector Cutoff Current						
at V _{CB} =60V		I _{CBO}	-	-	0.1	μΑ
Emitter Cutoff Current						
at V _{EB} =5V		I _{EBO}	-	-	0.1	μΑ
Collector Saturation Voltage	e					
at I _C =10mA, I _B =1mA		$V_{\text{CE(sat)}}$	-	-	0.3	V
Gain Bandwidth Product						
at V _{CE} =6V, I _C =1mA		f _T	-	150	-	MHz
Output Capacitance						
at V _{CB} =10V, f=1MHz		C_OB	-	2	-	pF
Noise Figure						
at V _{CE} =6V, I _C =0.1mA						
f=100Hz, R_G =10K Ω		NF(1)	-	0.5	6	V
Noise Figure						
at V_{CE} =6V, I_{C} =0.1mA						
f=1KHz, R_G =10KΩ		NF(2)	-	0.2	3	V









SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company